Power MOSFETS

DATASHEET

LM60J90DEE6A

Dual N-Channel

Enhancement Mode MOSFET

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Quality Management Systems

ISO 9001:2015 Certificate

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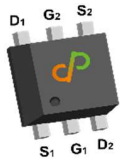
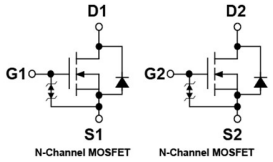
Pin Description

SOT-563 (TOP view)	Symbol
	

Ordering Information

Symbol	Dual N-Channel	Unit
V_{DSS}	**60**	**V**
$R_{DS(ON)\text{-}Max}$	**1.9**	**Ω**
I_D	**0.33**	**A**

Feature

- Reliable and Rugged
- ROHS Compliant & Halogen-Free
- ESD Protection

Applications

- Load Switch

Ordering Information

Orderable Part Number	Package Type	Form	Shipping	Marking
LM60J90DEE6A	SOT-563	Tape & Reel	3000 / Tape & Reel	4□□□

Note：□□□= Lot Code

Absolute Maximum Ratings (T_J=25°C Unless Otherwise Noted)

Symbol	Parameter		Dual N-Channel	Unit
V_{DSS}	Drain-Source Voltage		60	V
V_{GSS}	Gate-Source Voltage		±20	
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_{DM}①	Pulse Drain Current Tested	T_A=25°C	0.82	A
I_D①	Continuous Drain Current	T_A=25°C	0.33	A
		T_A=70°C	0.26	
P_D	Maximum Power Dissipation	T_A=25°C	0.42	W
		T_A=70°C	0.27	

Thermal Characteristics

Symbol	Parameter		Rating	Unit
$R_{\theta JA}$③	Thermal Resistance-Junction to Ambient	Steady State	300	°C/W

Note ①：Max. current is limited by Bonding wire

Note ②：UIS tested and pulse width are limited by maximum junction temperature 150˚C

Note ③：Device mounted on an FR4 PCB, single-sided copper , tin-plated and standard footprint.

Dual N-Channel Electrical Characteristics (T_J=25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250uA	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=48V, V_{GS}=0V	-	-	1	uA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250uA	1	1.6	2.5	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±10	uA
$R_{DS(ON)}$④	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=0.3A	-	1.6	1.9	Ω
		V_{GS}=4.5V, I_{DS}=0.2A	-	1.7	2.2	
gfs	Forward Transconductance	V_{DS}=10V, I_{DS}=0.15A	-	0.45	-	S
Dynamic Characteristics ⑤						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=30V, Freq.=1MHz	-	26.1	-	pF
C_{oss}	Output Capacitance		-	2.7	-	
C_{rss}	Reverse Transfer Capacitance		-	1.7	-	
$td_{(ON)}$	Turn-on Delay Time	V_{GS}=10V,V_{DS}=30V, I_D=0.3A,R_{GEN}=10Ω	-	1	-	nS
t_r	Turn-on Rise Time		-	19.3	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	23.2	-	
t_f	Turn-off Fall Time		-	21	-	
Q_g	Total Gate Charge	V_{GS}=4.5V,V_{DS}=30V I_D=1A	-	0.9	-	nC
Q_g	Total Gate Charge	V_{GS}=10V,V_{DS}=30V, I_D=1A	-	1.7	-	
Q_{gs}	Gate-Source Charge		-	0.4	-	
Q_{gd}	Gate-Drain Charge		-	0.3	-	
Source-Drain Characteristics						
V_{SD}④	Diode Forward Voltage	I_{SD}=0.15A, V_{GS}=0V	-	0.8	1.1	V
t_{rr}	Reverse Recovery Time	I_F=0.1A, V_R=0V dI$_F$/dt=100A/μs	-	7.4	-	nS
Q_{rr}	Reverse Recovery Charge		-	2.4	-	nC

Note ④：Pulse test (pulse width300us, duty cycle2%).
Note ⑤：Guaranteed by design, not subject to production testing

N-Channel Typical Characteristics

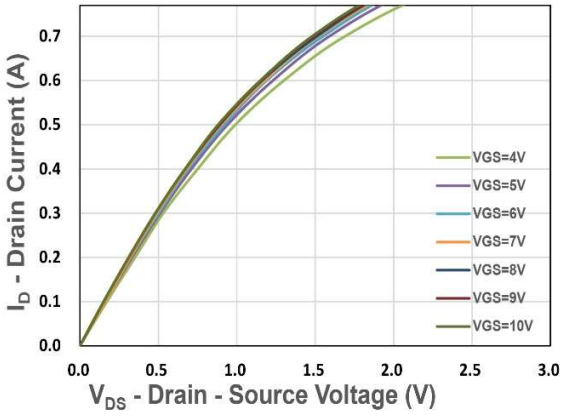


Figure 1. Output Characteristics

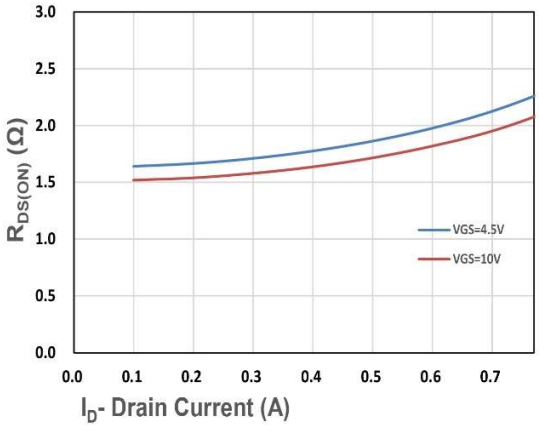


Figure 2. On-Resistance vs. ID

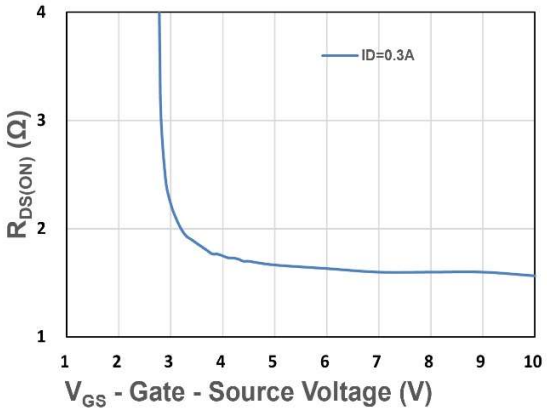


Figure 3. On-Resistance vs. VGS

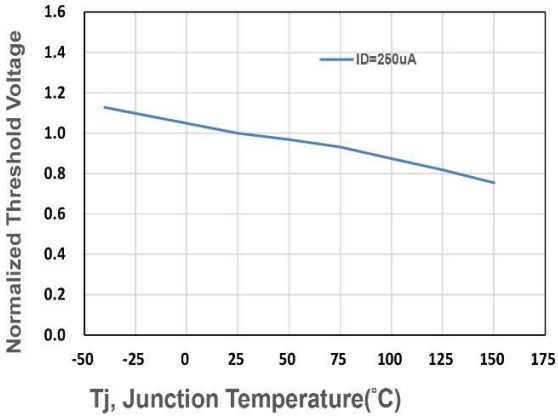


Figure 4. Gate Threshold Voltage

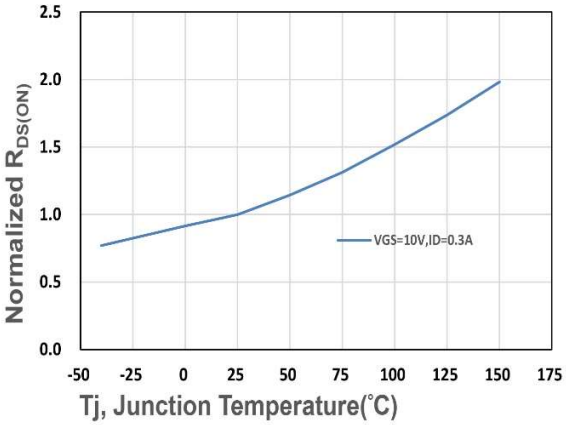


Figure 5. Drain-Source On Resistance

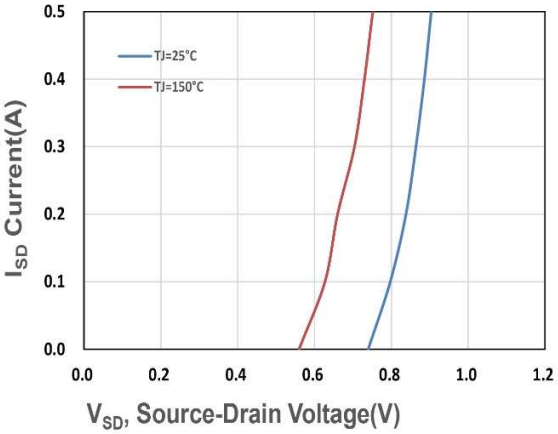


Figure 6. Source-Drain Diode Forward

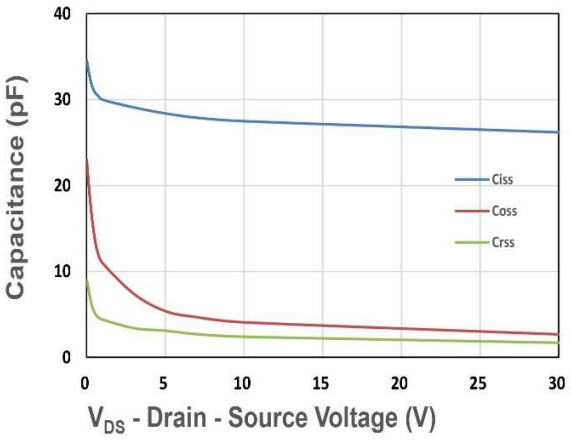


Figure 7. Capacitance

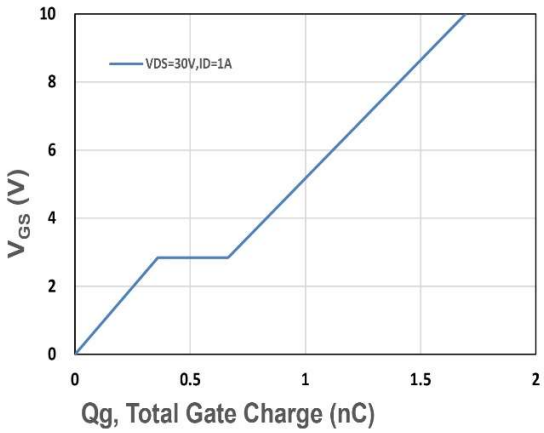


Figure 8. Gate Charge Characteristics

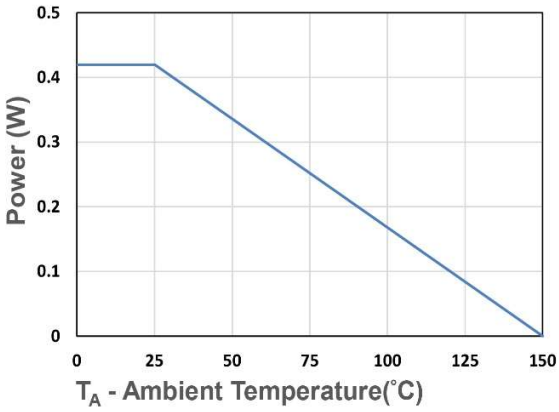


Figure 9. Power Dissipation

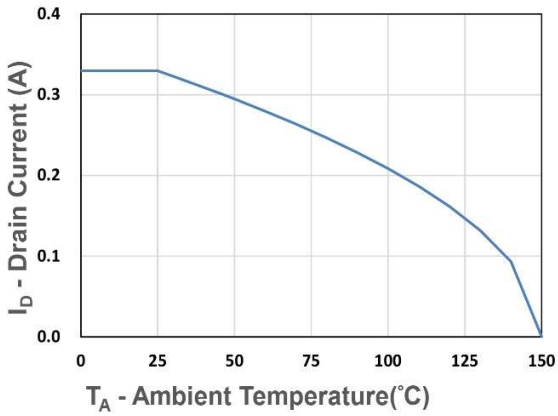


Figure 10. Drain Current

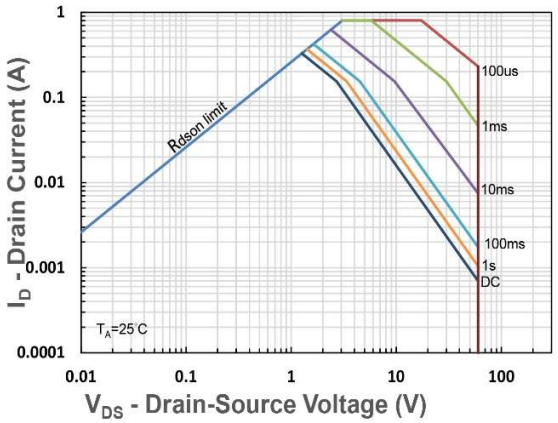


Figure 11. Safe Operating Area

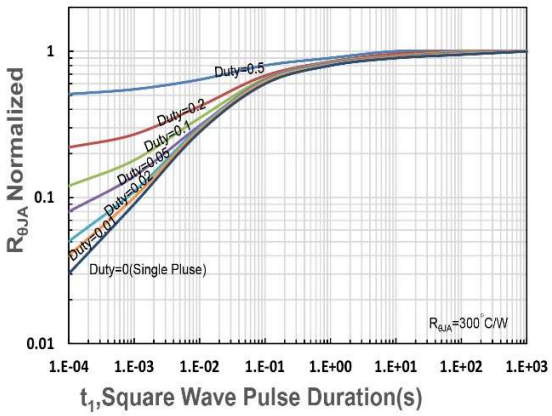


Figure 12. RθJA Transient Thermal Impedance